



### **Features**

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low R<sub>DS</sub>(on)
- Operated at Low Logic Level Gate Drive

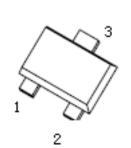
### **Product Summery**

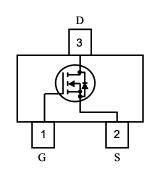
BVDSS	RDSON (TYP.)	ID (MAX)
20V	240mΩ	
20V	280mΩ	0.6A
20V	410mΩ	0.07
20V	450mΩ	

# **Applications**

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

### **SOT-723 Pin Configuration**





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 8$	V
I <sub>D</sub> @T <sub>A</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	400	mA
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	1.2	Α
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	0.150	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient (note 1)	823	°C/W
TJ	Junction Temperature	150	$^{\circ}\! \mathbb{C}$
T <sub>STG</sub>	Storage Temperature Range -55 to 150		$^{\circ}\!\mathbb{C}$
TL	Lead Temperature for Soldering Purposes(1/8" from case for 10 s) 260		$^{\circ}\!\mathbb{C}$

**N-Ch MOSFET** 

## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	20			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.05		V/°C	
	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.4A		240	450		
R <sub>DS(ON)</sub>		V <sub>GS</sub> =2.5V , I <sub>D</sub> =0.3A 280		280	765	mΩ	
T CDS(ON)		V <sub>GS</sub> =1.8V , I <sub>D</sub> =0.2A		410	850	<del>-</del> mΩ	
		V <sub>GS</sub> =1.5V , I <sub>D</sub> =0.1A		450	950		
V <sub>GS(th)</sub>	Gate Threshold Voltage	\/ -\/   -250A	0.35		1.0	V	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA		-3.7		mV/℃	
	Drain-Source Leakage Current	V <sub>DS</sub> =16V , V <sub>GS</sub> =0V , T <sub>J</sub> =25℃			1		
I <sub>DSS</sub>		V <sub>DS</sub> =16V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃			5	uA uA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 8V$ , $V_{DS}$ =0V			±10	uA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =0.1A		1.5		S	
T <sub>d(on)</sub>	Turn-On Delay Time			5.8			
Tr	Rise Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,		2.9			
T <sub>d(off)</sub>	Turn-Off Delay Time	$R_G=6\Omega$ , $I_D=0.1A$		18		ns	
Tf	Fall Time			9			
C <sub>iss</sub>	Input Capacitance			88			
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		15		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			10			

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V =V =0V Force Current			100	mA
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			0.5	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =0.2A , T <sub>J</sub> =25℃			1.2	V

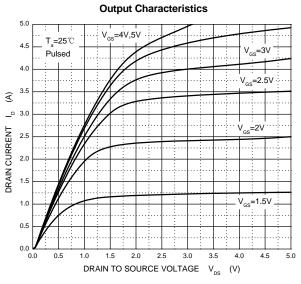
### Notes:

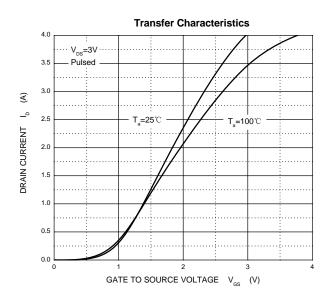
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.

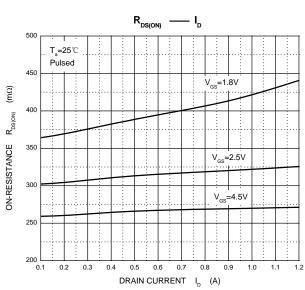


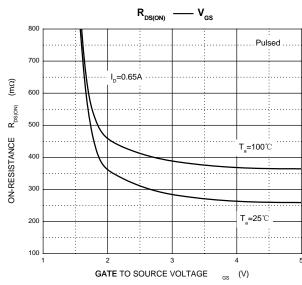
**N-Ch MOSFET** 

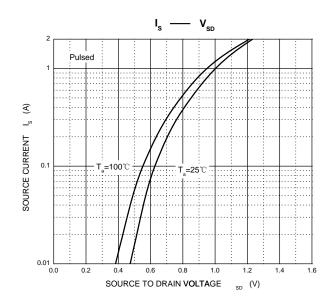
### **Typical Performance Characteristics**

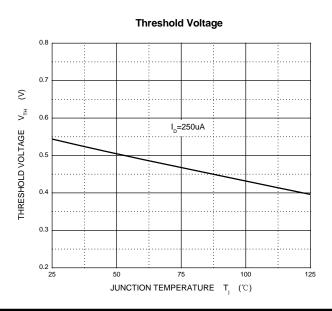






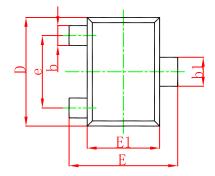


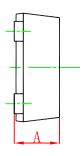


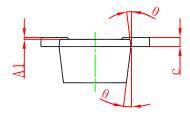




# **SOT-723 Package Outline Dimensions**

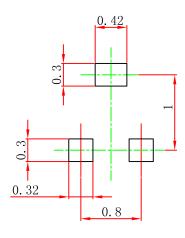






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.430	0.500	0.017	0.020	
A1	0.000	0.050	0.000	0.002	
b	0.170	0.270	0.007	0.011	
b1	0.270	0.370	0.011	0.015	
С	0.080	0.150	0.003	0.006	
D	1.150	1.250	0.045	0.049	
Е	1.150	1.250	0.045	0.049	
E1	0.750	0.850	0.030	0.033	
е	0.800TYP.		0.03	0.031TYP.	
θ	7° F	7° REF. 7° REF.		REF.	

### **SOT-723 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

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